

POWERED BY **Dialog****PRODUCTION OF THIN-FILM TRANSISTOR (03-102324****Publication Number:** JP 3102324 A) , April 26, 1991**Inventors:**

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**Applicants**

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**Application Number:** 01-241511 (JP 89241511) , September 18, 1989**International Class (IPC Edition 5):**

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**JAPIO Class:**

- 29.2 (PRECISION INSTRUMENTS--- Optical Equipment)
- 42.2 (ELECTRONICS--- Solid State Components)

**JAPIO Keywords:**

- R011 (LIQUID CRYSTALS)

**Abstract:**

**PURPOSE:** To shorten the time for production and to reduce the cost of production by forming an insulating film for a gate or insulating film for a protective film by a printing method using a coating material of a silicon system.

**CONSTITUTION:** The noncrystalline insulating film 3 for the gate of the thin-film transistor (TFT) and the noncrystalline insulating film 5 for the protective film of the channel part as well as the noncrystalline insulating film 8 for protecting the entire part of the TFT are applied and formed by the printing method using the coating material of the silicon system. The need for the stages for applying, exposing and developing a photoresist, etc., is eliminated and the time for production is shortened as compared with the film formation by the conventional plasma CVD. The need for a photomask, resist, developer, etc., is eliminated and the cost of production is reduced; in addition, the productivity is improved. (From: *Patent Abstracts of Japan*, Section: P, Section No. 1231, Vol. 15, No. 296, Pg. 53, July 26, 1991 )

**JAPIO**

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